SL05T1G Series

ESD Protection Diode
Low Capacitance

This family of surge protection offers transient overvoltage protection with significantly reduced capacitance. The capacitance is lowered by integrating a compensating diode in series. This integrated solution offers ESD protection for high speed interfaces such as communication systems, computers, and computer peripherals.

Features

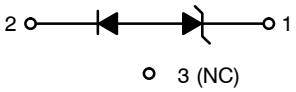
- Surge protection Diode in Series with a Compensating Diode Offers <5 pF Capacitance
- ESD Protection Meeting IEC 61000−4−2, 4−4, 4−5
- Peak Power Rating of 300 W, 8 × 20 μs
- Bi−Direction Protection Can Be Achieved By Using Two Devices
- Flammability Rating UL 94 V−0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

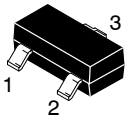
Mechanical Characteristics:
CASE: Void-free, transfer-molded, thermosetting plastic case
FINISH: Corrosion resistant finish, easily solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260°C for 10 Seconds
Package designed for optimal automated board assembly
Small package size for high density applications
Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel.
Replace the “T1” with “T3” in the Device Number to order the 13 inch/10,000 unit reel.

ON Semiconductor®

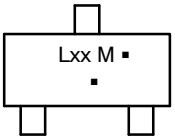
www.onsemi.com





SOT−23 (TO−236)
CASE 318
STYLE 26

MARKING DIAGRAM



Lxx = Device Code
xx = 05, 12, 15, or 24
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
SL05T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SZSL05T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SL12T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SZSL12T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SL15T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SZSL15T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SL24T1G	SOT−23 (Pb−Free)	3000/Tape & Reel
SZSL24T1G	SOT−23 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 2 of this data sheet.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 8x20 usec (Note 1) @ $T_L \le 25°C$	P_{pk}	300	W
IEC 61000−4−2 Level 4	V_{pp}		
Contact Discharge		±8	kV
Air Discharge		±16	kV
IEC 61000−4−4 EFT		40	A
IEC 61000−4−5 Lightning		12	A
Total Power Dissipation on FR−5 Board (Note 2) @ $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	− 55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

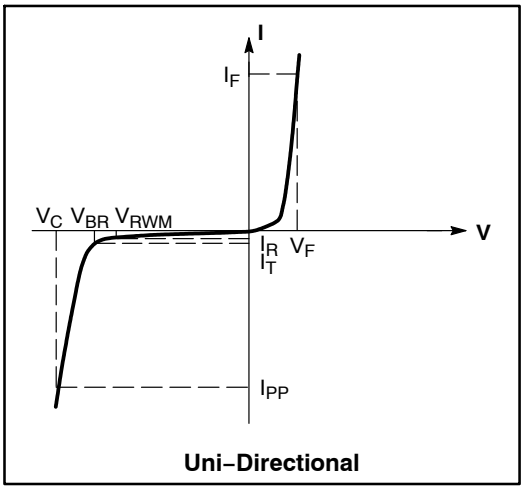
1. Non−repetitive current pulse per Figure 2
2. FR−5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



Uni−Directional

ELECTRICAL CHARACTERISTICS

Device	Device Marking	V_{RWM} (V)	I_R @ V_{RWM} (μA)	Breakdown Voltage (Note 4) V_{BR} @ 1 mA (Volts) Min	Breakdown Voltage (Note 4) V_{BR} @ 1 mA (Volts) Max	V_C, Clamping Voltage (Note 5) @ 1 A (V)	V_C, Clamping Voltage (Note 5) @ 5 A (V)	Max I_{PP} (A)	Capacitance @ V_R = 0 V, 1 MHz (pF) Typ	Capacitance @ V_R = 0 V, 1 MHz (pF) Max
SL05	L05	5.0	20	6.0	8.0	9.8	11	17	3.5	5.0
SL12	L12	12	1.0	13.3	15.5	19	24	12	3.5	5.0
SL15	L15	15	1.0	16.7	18.5	24	30	10	3.5	5.0
SL24	L24	24	1.0	26.7	29	43	55	5.0	3.5	5.0

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. V_{BR} measured at pulse test current of 1 mA at an ambient temperature of 25°C
5. Surge current waveform per Figure 2

TYPICAL CHARACTERISTICS

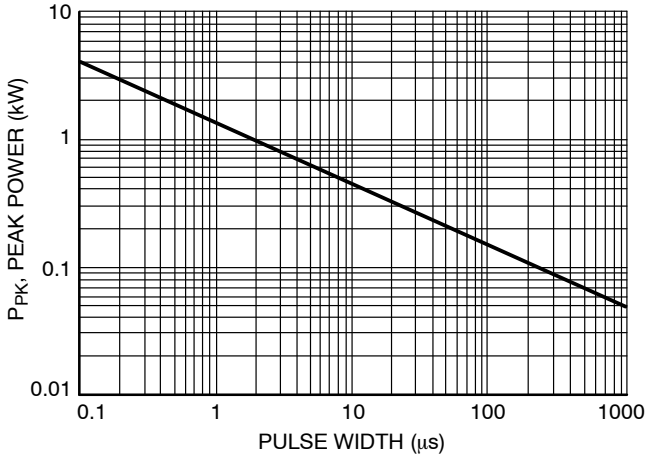


Figure 1. Maximum Peak Power Rating

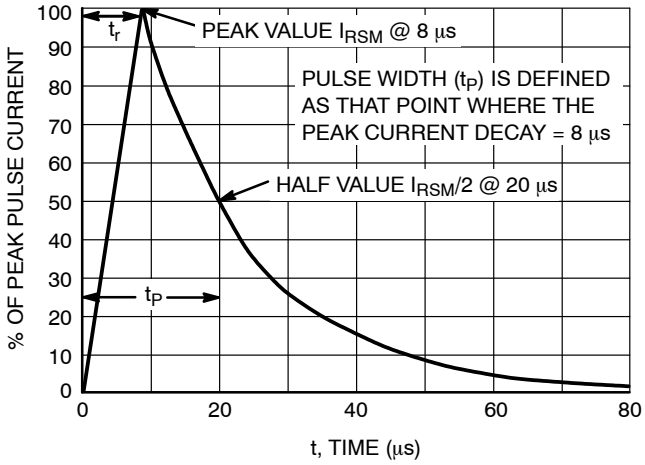


Figure 2. 8 × 20 μs Pulse Waveform

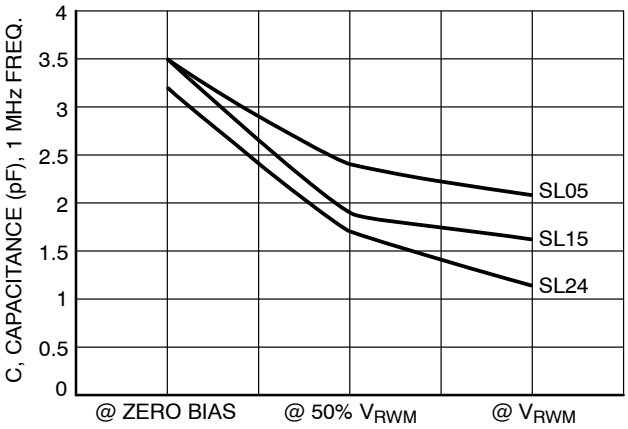


Figure 3. Typical Junction Capacitance

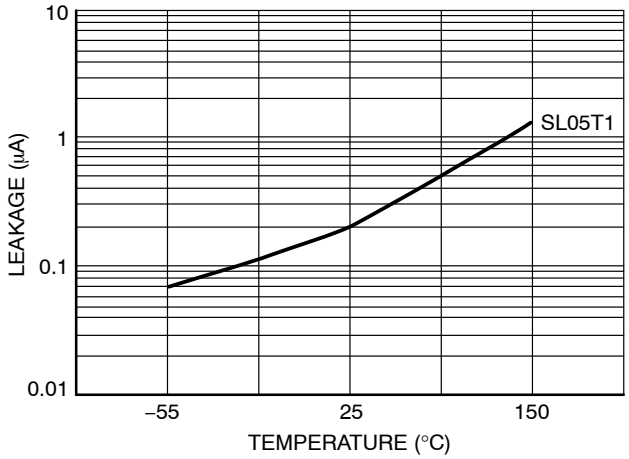


Figure 4. Typical Leakage Over Temperature

Applications Background

This family of surge protection devices (SL05T1 series) are designed to protect sensitive electronics such as communications systems, computers, and computer peripherals against damage due to ESD conditions or transient voltage conditions. Because of their low capacitance value (less than 5 pF), they can be used in high speed I/O data lines. Low capacitance is achieved by integrating a compensating diode in series with the surge protection which is basically based in the below theoretical principle:

- Capacitance in parallel: CT = C1+C2+....+Cn
- Capacitance in series: 1/CT = (1/C1)+(1/C2)+....+(1/Cn)

The Figure 5 shows the integrated solution of the SL05T1 series device:

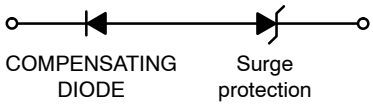


Figure 5.

In the case that an over−voltage condition occurs in the I/O line protected by the SL05T1 series device, the surge protection is reversed−biased while the compensation diode is forward−biased so the resulting current due to the transient voltage is drained to ground.

If protection in both polarities is required, an additional device is connected in inverse−parallel with reference to the first one, the Figure 6 illustrates the inverse−parallel connection for bi−directional or unidirectional lines:

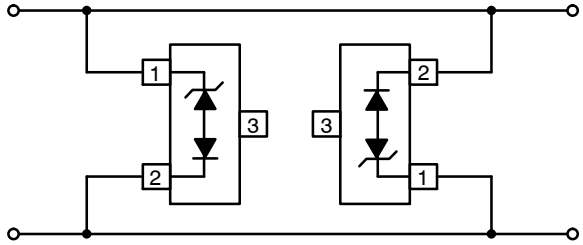


Figure 6.

An alternative solution to protect unidirectional lines, is to connect a fast switching steering diode in parallel with the SL05T1 series device. When the steering diode is forward−biased, the surge protection will avalanche and conduct in reverse direction. It is important to note that by adding a steering diode, the effective capacitance in the circuit will be increased, therefore the impact of adding a steering diode must be taken in consideration to establish whether the incremental capacitance will affect the circuit functionality or not. The Figure 7 shows the connection between the steering diode and the SL05T1 series device:

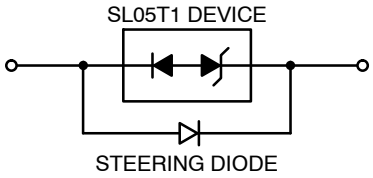


Figure 7.

Another typical application in which the SL05T1 series device can be utilized, is to protect multiple I/O lines. The protection in each of the I/O lines is achieved by connecting two devices in inverse−parallel. The Figure 8 illustrates how multiple I/O line protection is achieved:

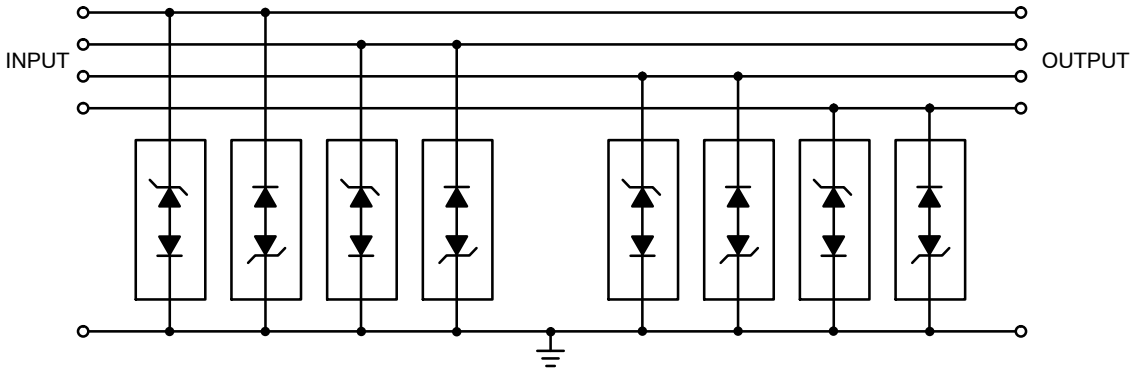
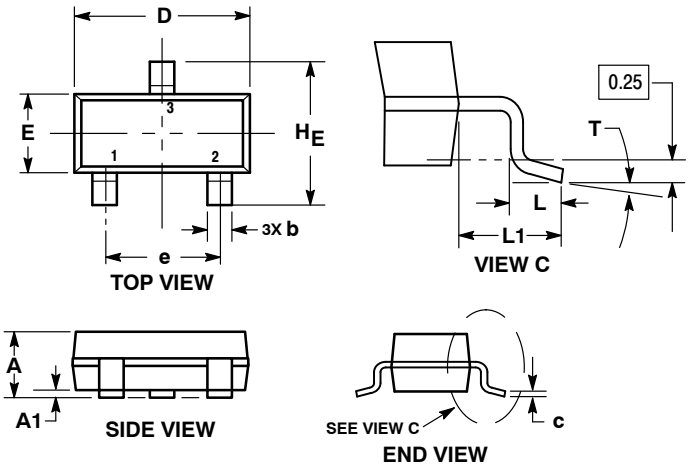


Figure 8.

For optimizing the protection, it is recommended to use ground planes and short path lengths to minimize the PCB's ground inductance.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

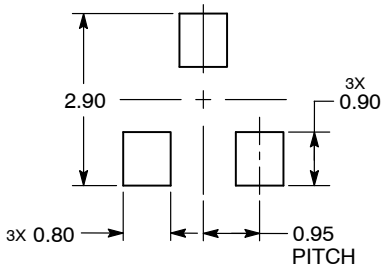


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	–––	10°	0°	–––	10°

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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